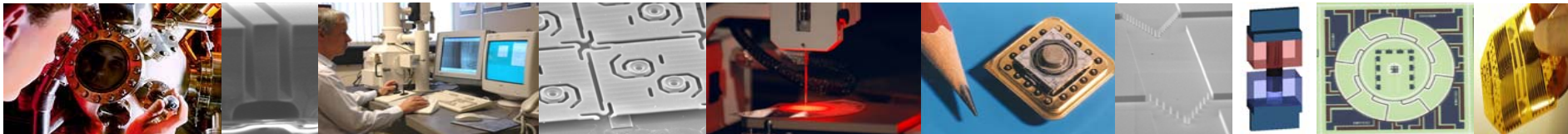


Aspects of Micropackaging and System Integration of MEMS Devices

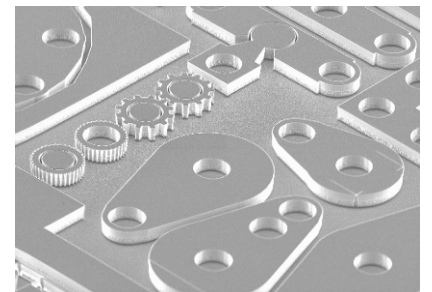
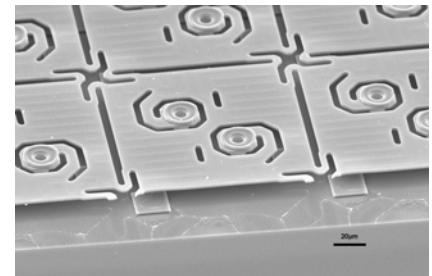
Advanced Technology Centre – Bristol, UK

Alan Pritchard, Ian Sturland



Summary

- MEMS for SPACE
 - A low volume specialised requirement for
 - MEMS Sensors, Actuators, Structures
 - Novel Packaging solutions required for optimum system performance
- Issues associated with niche MEMS products e.g. in Aerospace and Defence industries
 - Where to get qualified devices made
 - Novel Packaging
- Manufacturing routes
 - MEMS fab and packaging for Space Environment
- Examples
 - Development of Space Gyro
 - RF MEMS
 - Aerodynamic Flow control
 - Digital Sun Tracker
- Conclusion
 - A flexible design, proof of principle and niche volume manufacture of MEMS devices for Space Applications is possible.



Development of MEMS Gyro for Space

BAE Systems involved with development Si MEMS gyros since mid 1990's

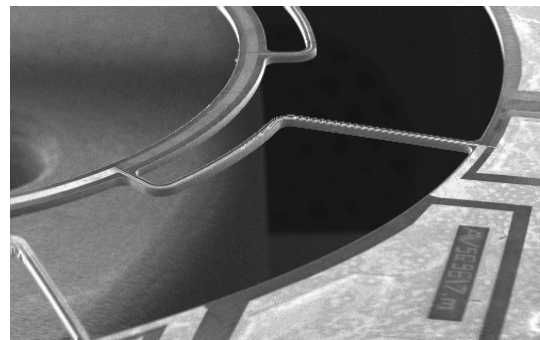
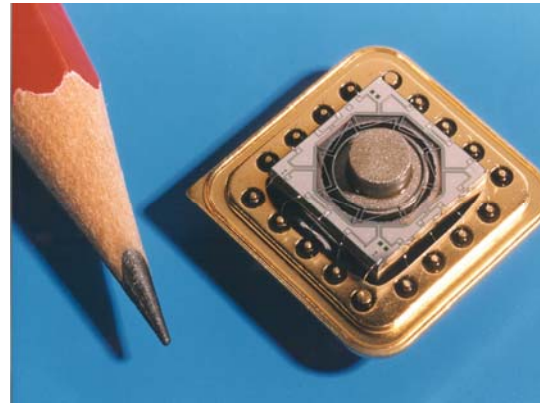
Inertial Sensor Business - originally a BAE Systems Company activity, now Atlantic Inertial Systems a Goodrich Company



First to market with a high volume commercial Si MEMS gyro

- Targeted at automotive applications with
- ~2 deg/sec bias drift
- Supplied >17 million units into automotive and commercial markets

Military
100 deg/hr & gun hard – integrated into IMU
– three gyros & three accelerometers
Very good performance over temp, shock, vibration



Development of MEMS Gyro for Space Requirements

MRS Key Target Parameters

Target specifications	
Configuration	- 3-axis/rate mode - <4W/600g unit
Bias stability (3σ) over 24 hours, $\Delta T < \pm 10^\circ\text{C}$	< 5 deg/h
Angular Random Walk	< 0.2 deg/ $\sqrt{\text{h}}$
Range	Up to 20 deg/s
Output Rate	1-10 Hz
Command/Monitor I/F	RS422 async channels (SpaceWire)
Rate Outputs	RS422 async channels Analogue Channels

MEMS is enabling technology for required low mass, power, cost.

Positions MEMS gyro for:

- initial acquisitions
- anomaly detection
- anomaly recovery
- safe mode applications.

Modest rate range and output bandwidth compared to normal MEMS applications.

Simple User Interfaces



Development of MEMS Gyro for Space

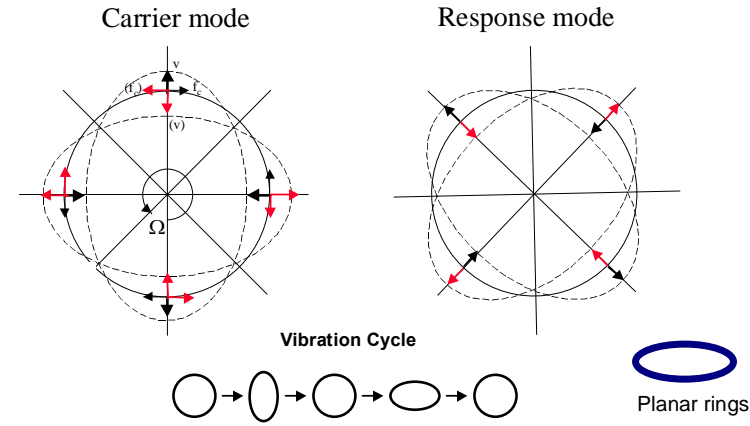
- Use DRIE Si Resonant vibrating ring structure (as previous commercial and military products).
- Small gaps, high aspect ratio
- Small AC signals – need low parasitic capacitance

Glass substrate
(anodically bonded Glass-Si-Glass)

- Interconnect to asic and local JFET OpAmps
Through glass vias (analogue of TSV)
Powder blasted
Metalised

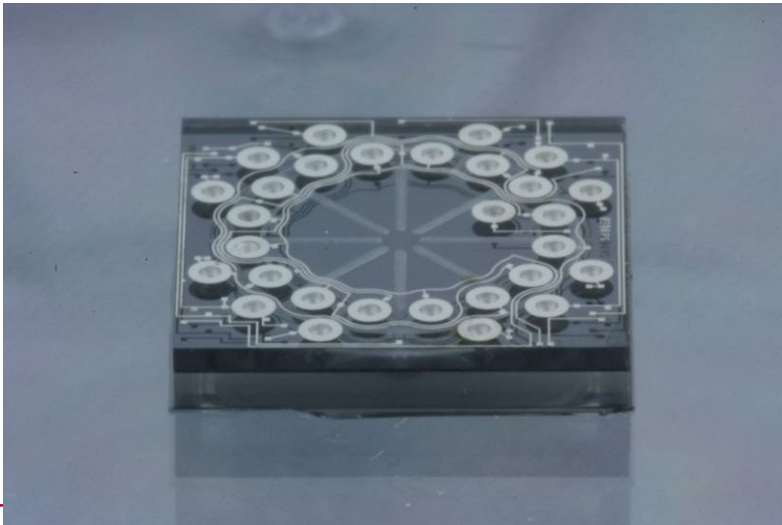
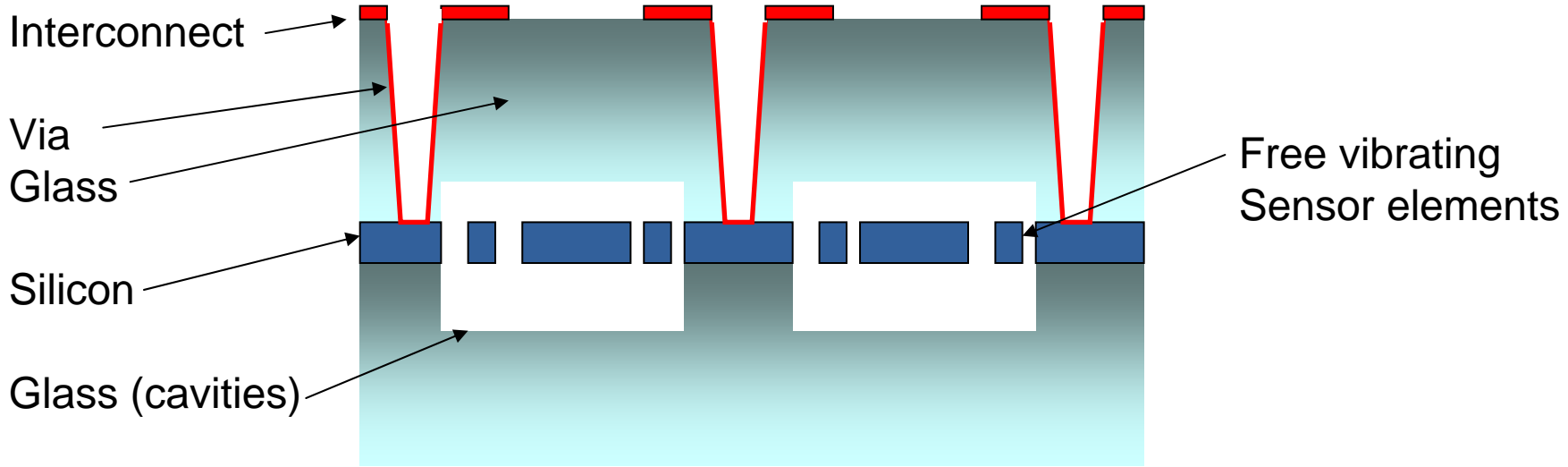
- In situ Vacuum and wafer scale packaging
- Rad Hard Electronics

Vibrating Structure Gyro Principles

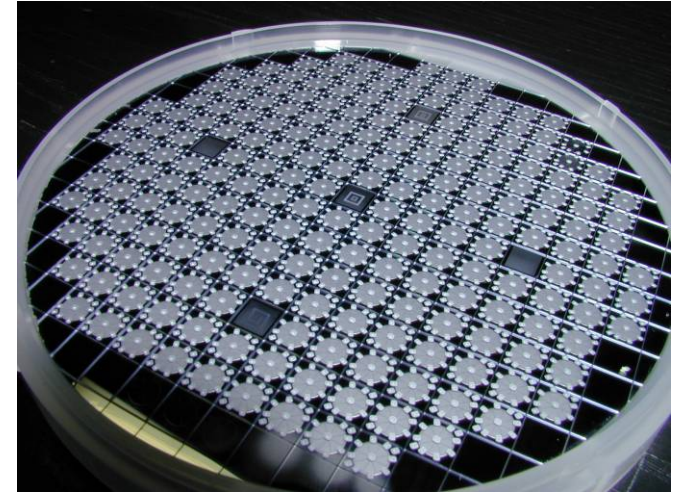
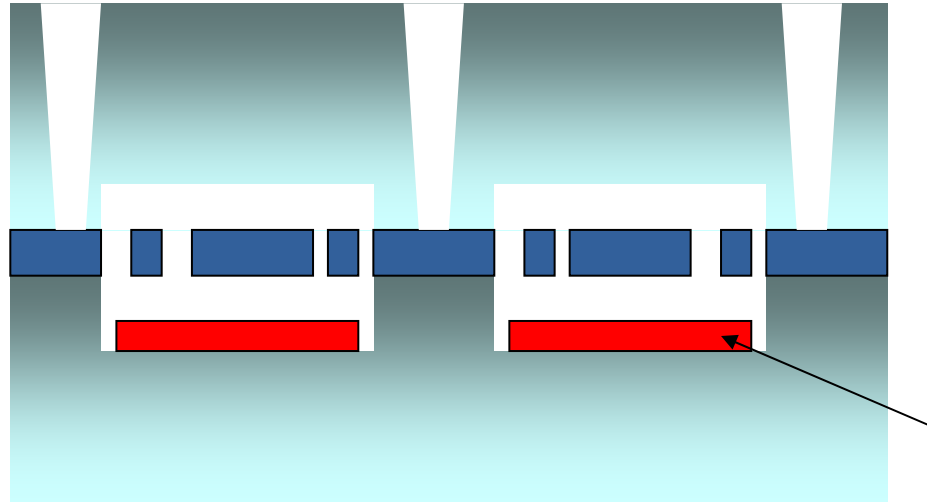


Development of MEMS Gyro for Space

Silicon on glass with through glass vias



Development of MEMS Gyro for Space Wafer level Vacuum Packaging



Getter

Thin film getter, PVD into glass cavities

Ensures long vacuum life even when SA/Vol ratio non ideal

Wafer bonding – can be anodic or glass frit

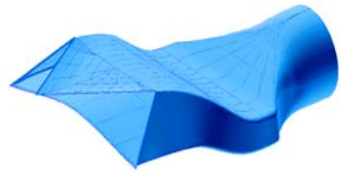
The MEMS Si Gyro now commercially available as SiREUS, a compact low power, low mass, 3 axis orthogonal Coarse Rate Sensor system



Opportunities for MEMS-based Flow Separation Control

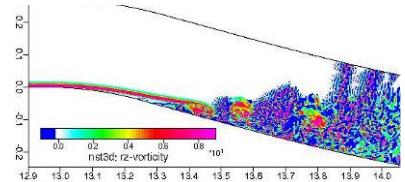
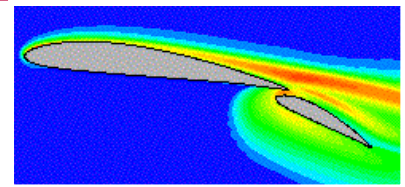
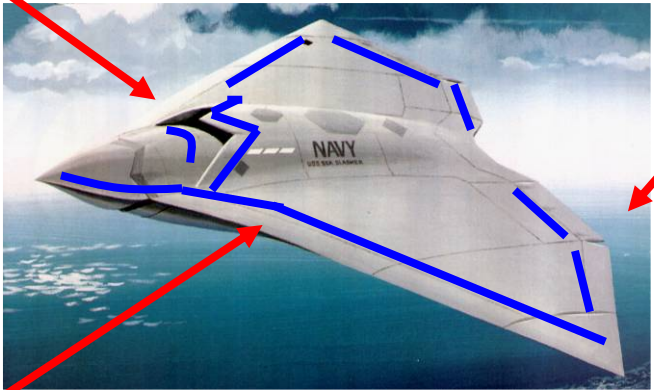
The Benefits

- Improved Performance
- Improved LO
- Reduced System Complexity/weight
- Increased Design Freedom



Propulsion and LO Propulsion Integration

- **Inlet distortion**
- **Pressure recovery**
- **Flow unsteadiness**
- **External / internal lip separation**
- Compressor stall/surge



Trailing Edge Control

- **High lift**
- **Manoeuvre**



Leading Edge Control

- Boundary layer and vortex control
- **High lift**
- **LO manoeuvre/stability**
- Buffet

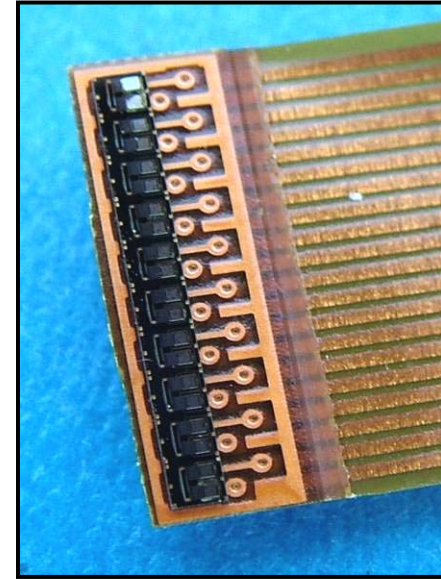
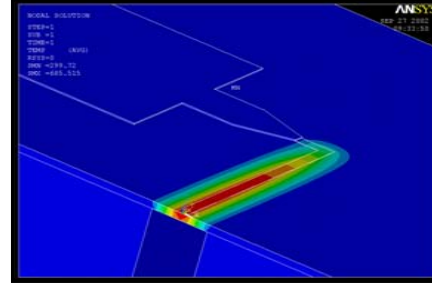
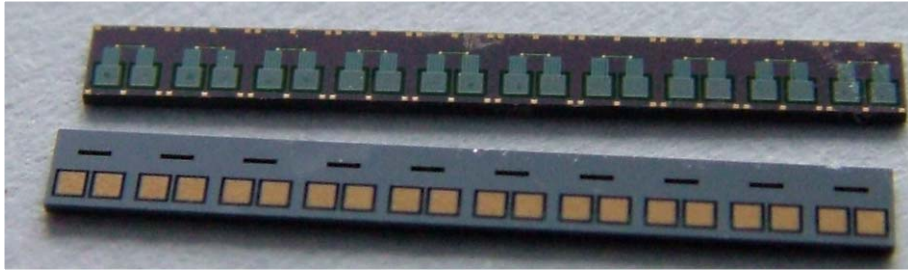


Low level periodic forcing modulates vortex rollup

Technology Demonstrated

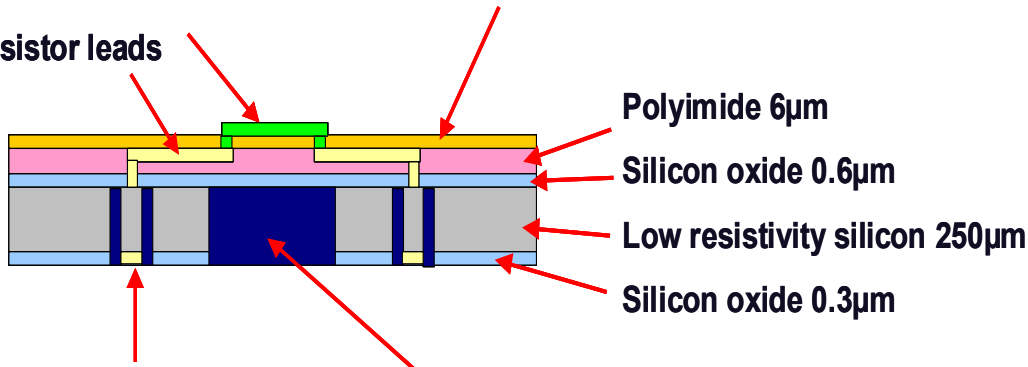
With non MEMS flight control
In FLAVIIR project

MEMS Flow Sensors



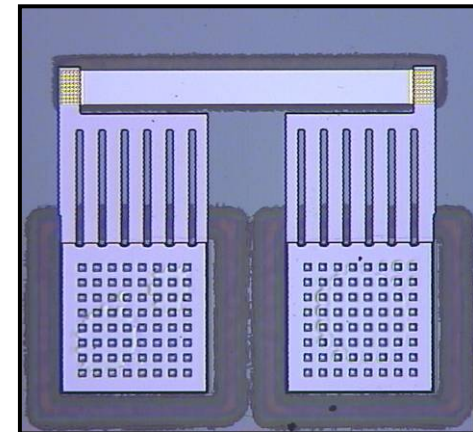
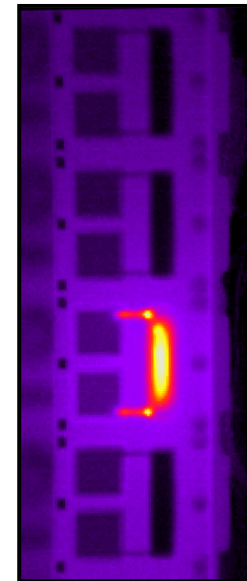
Tungsten resistor ~300nm **Silicon nitride top layer 1µm**

Resistor leads



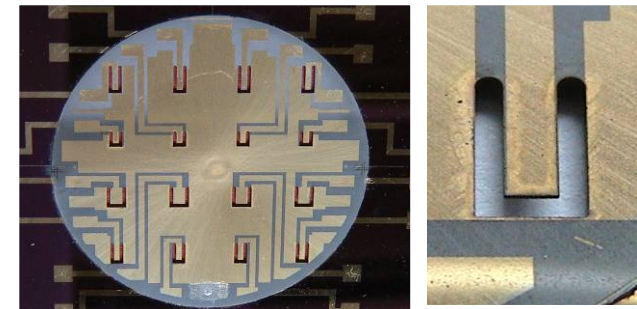
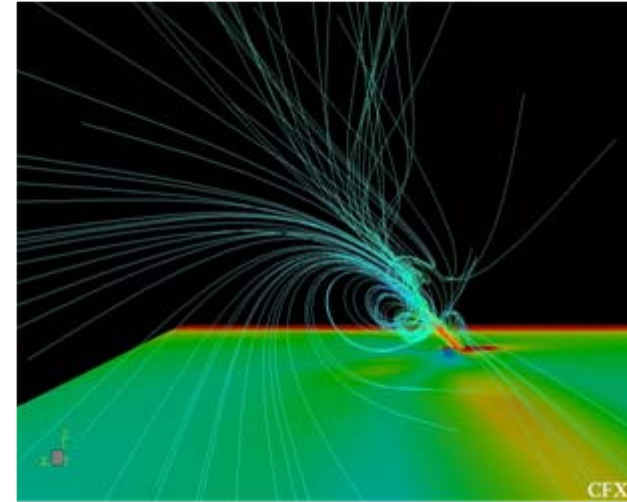
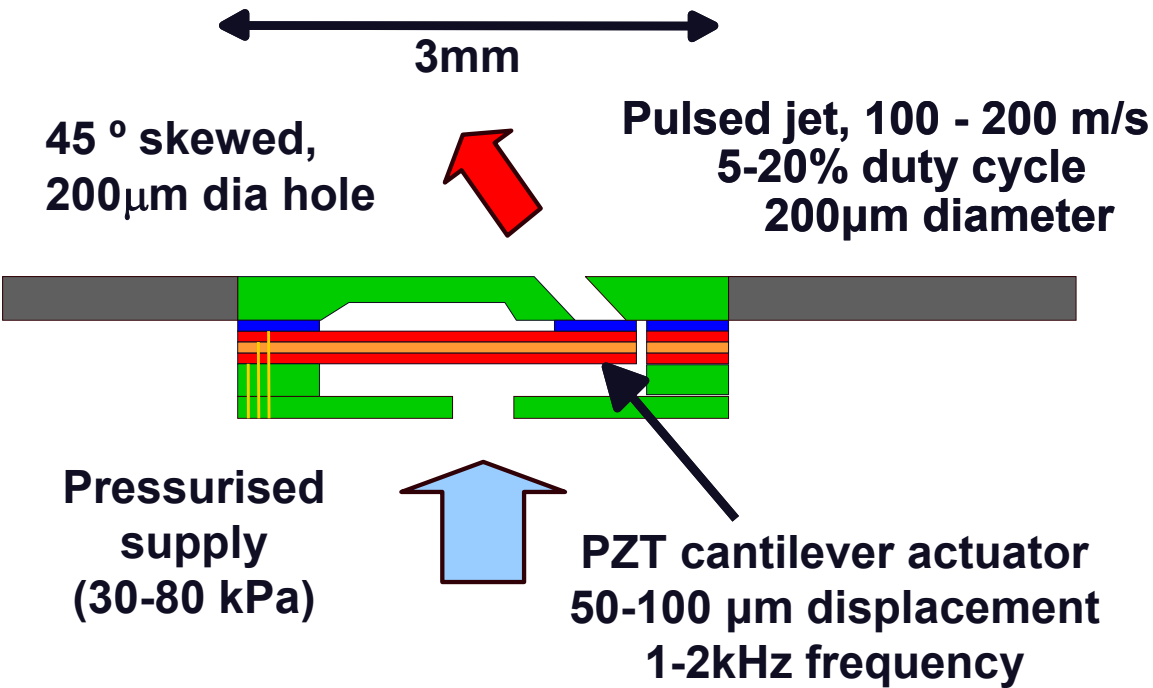
Through wafer connections

Membrane cavity



Designed for robustness, sensitivity, good frequency response
10 x sensitivity of conventional stick-on hot film, 30 kHz cut-off

MEMS Pulse-Jet Flow Actuator

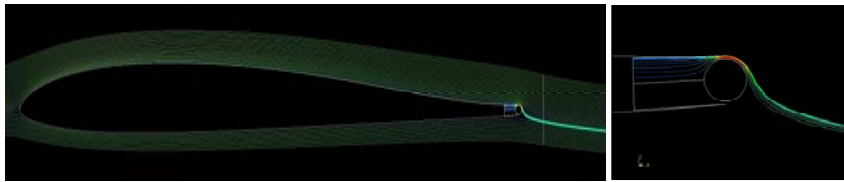
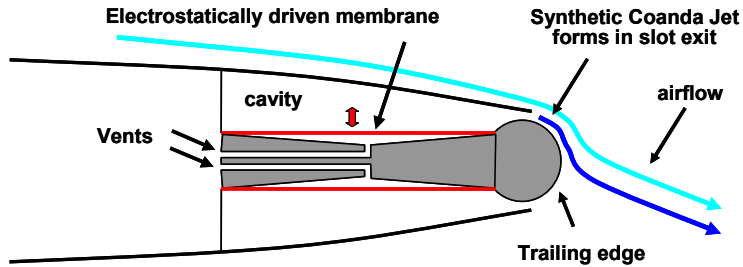


Robust, high authority (force & displacement), small footprint and thickness.

Bulk PZT properties Bonded & structured at wafer level

MEMS Coanda jet actuation for MAV

Full aero authority without moving parts



Precision silicon trailing edge box structures

150mm MAV



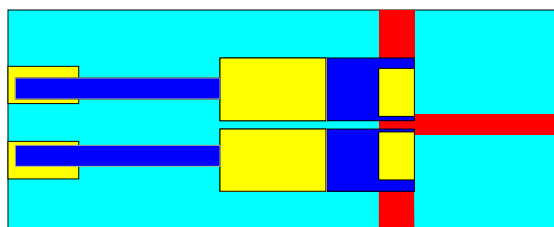
RF MEMS: MEMS components for RF circuits

Advantages:

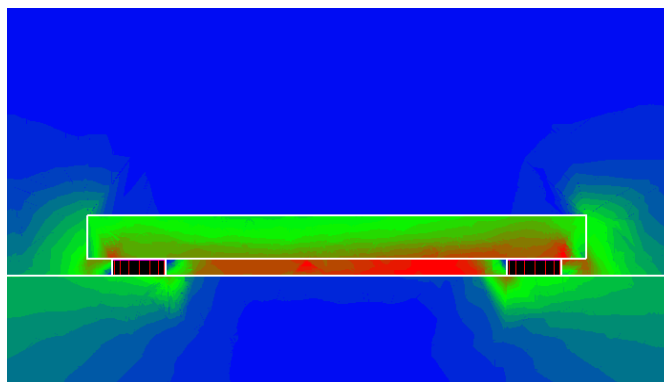
- size
- insertion loss
- Q factor
- cost
- linearity

Applications

- RADAR
- Electronic warfare



MEMS switch design



RF simulation

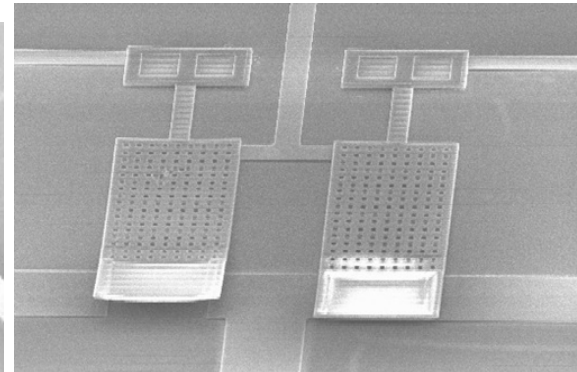
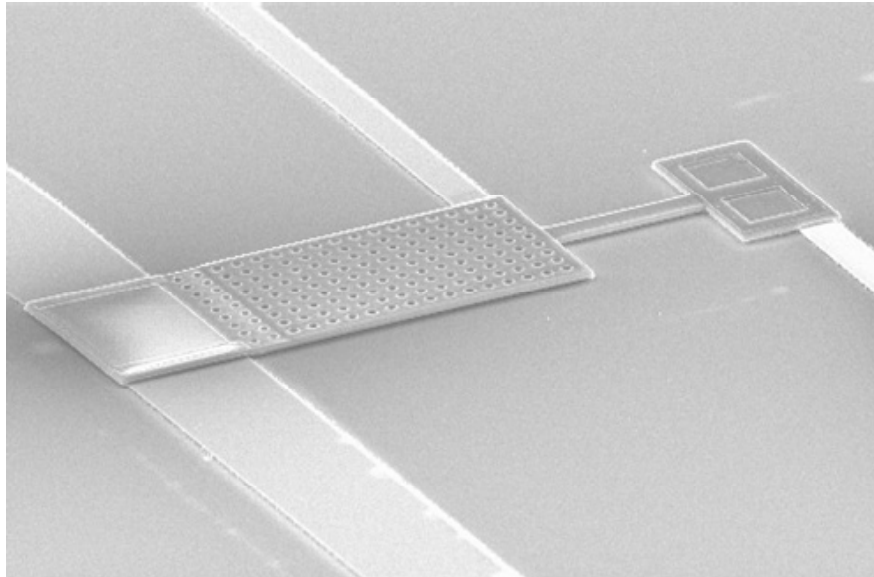
RF MEMS switches

Early cantilever design

RF in

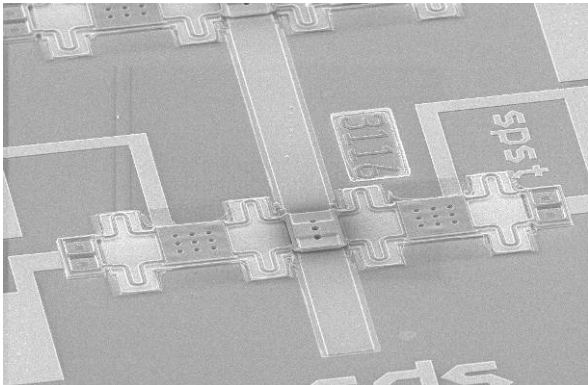
Contact up-down travel 3um

Control line



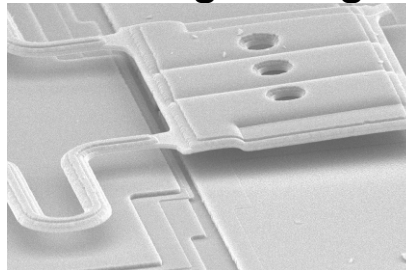
OFF

ON

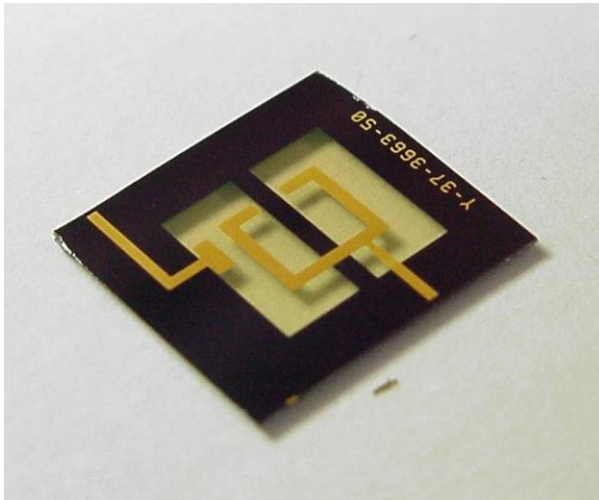


RF out

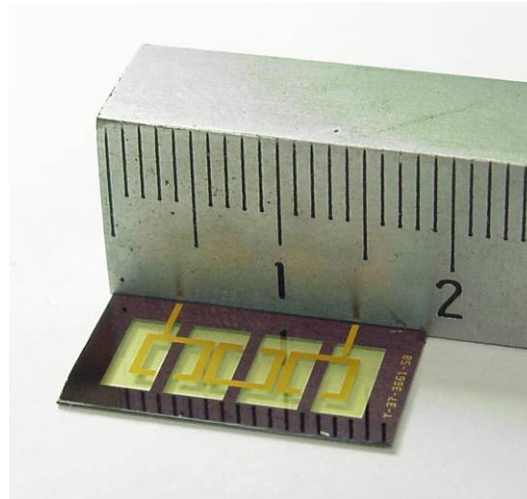
New bridge design



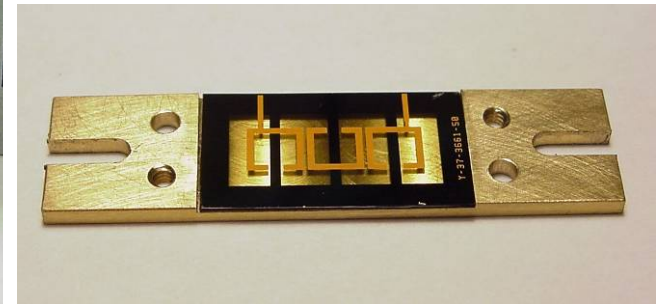
***Gold tracks on nitride membranes on silicon frames
(stackable) – give high Q (~3-400)***



Input resonator



complete 3 section filter



packaged filter

RF MEMS Technology

Switches

Vac Packaged – high Q
interface to phase delays

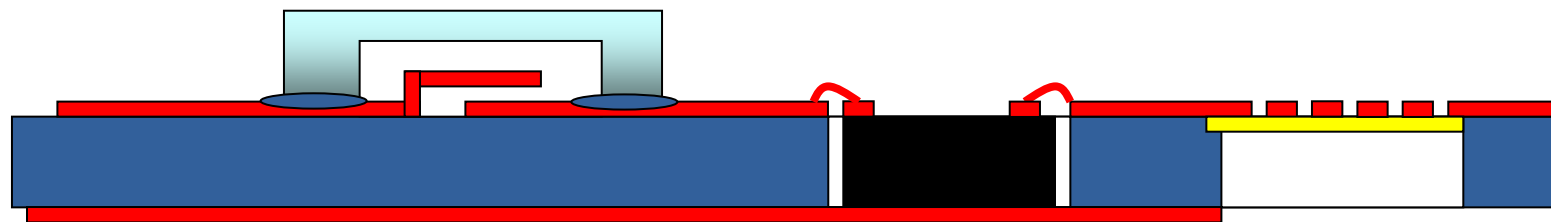
Phase Delays (microstrip)

Fairly large structures

GaAs Chips e.g Amplifiers interface (co-planar) to microstrip over Si

High Q Filters

Membranes “conductors in vacuum” dielectric



Switch and phase delay elements

GaAs Chip

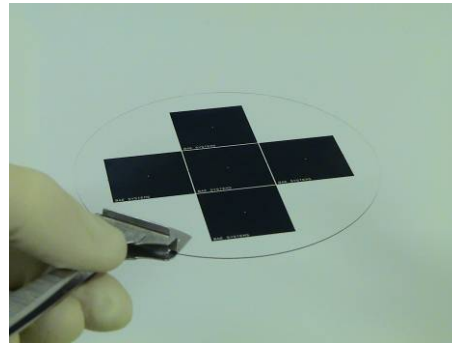
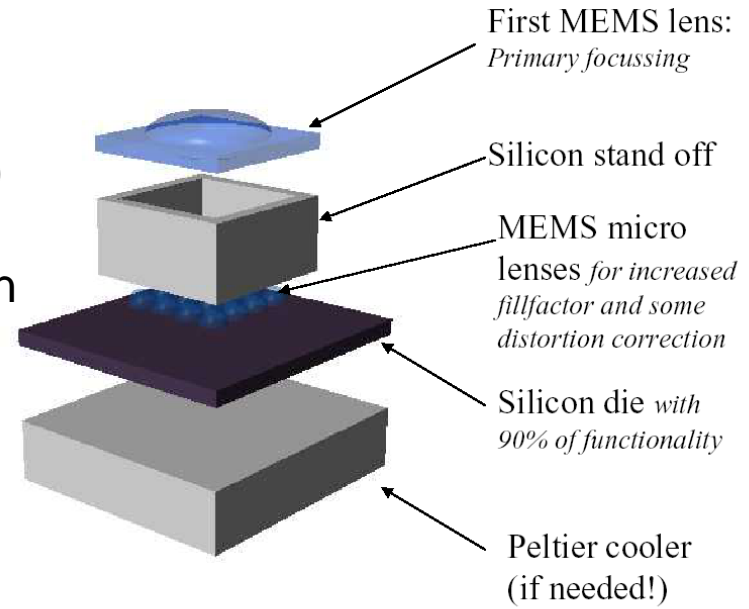
High Q Filters

ESA Sun Sensor on a chip project

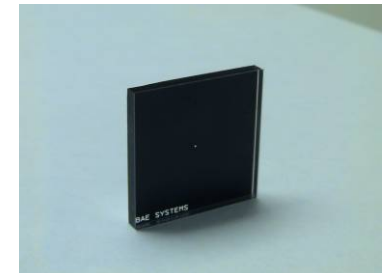
Concept

Create a low cost standard Sun Tracker product applicable to a wide range of Satellite (and Rover?) uses.

Use APS Imaging Chips and wafer scale integration & packaging techniques

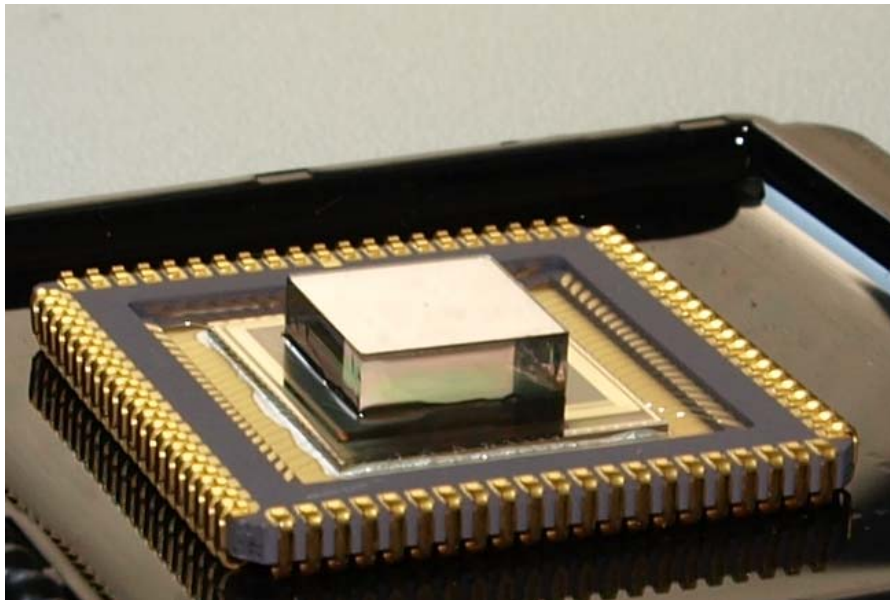


MEMS pinhole sandwich chips to be integrated directly with sensor chip



ESA Digital Sunsensor -Sun Sensor on Chip (SSoC)

Initial breadboard integrated device
-die level packaging not wafer level



Pinhole and chip bonded



Prime contractor overall instrument design



Design & Supply of APS Imaging Chip

BAE SYSTEMS

Advanced Technology Centre

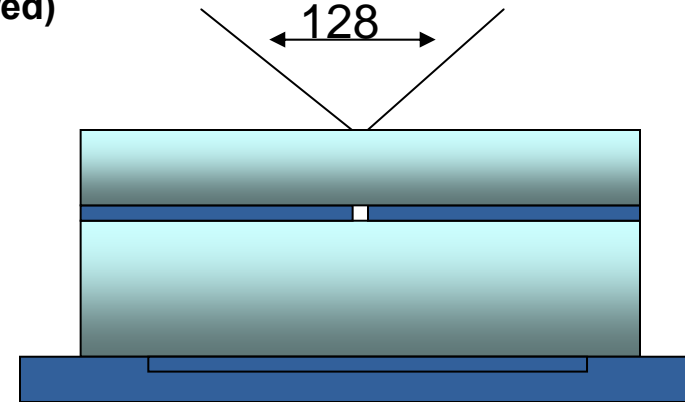
Design fabrication of Optical Chip
and Wafer Level Packaging

Digital Sun Sensor Specification

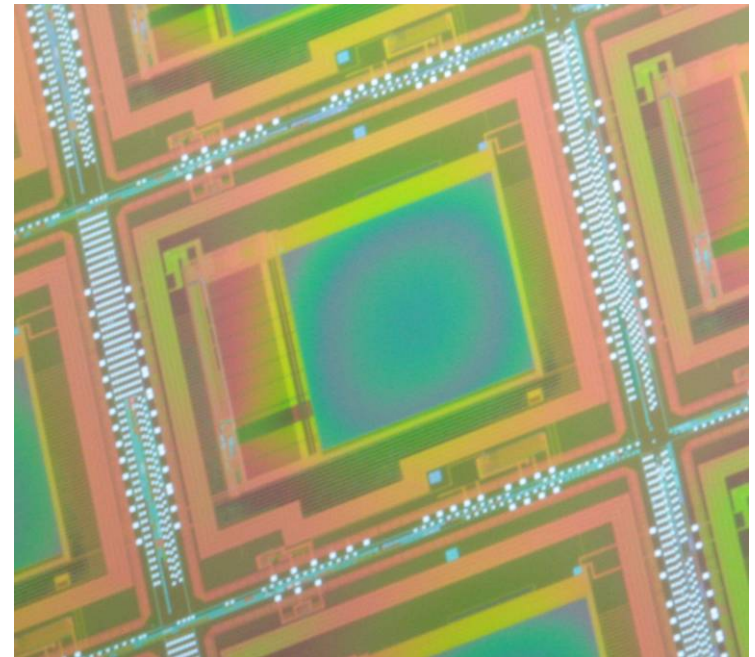
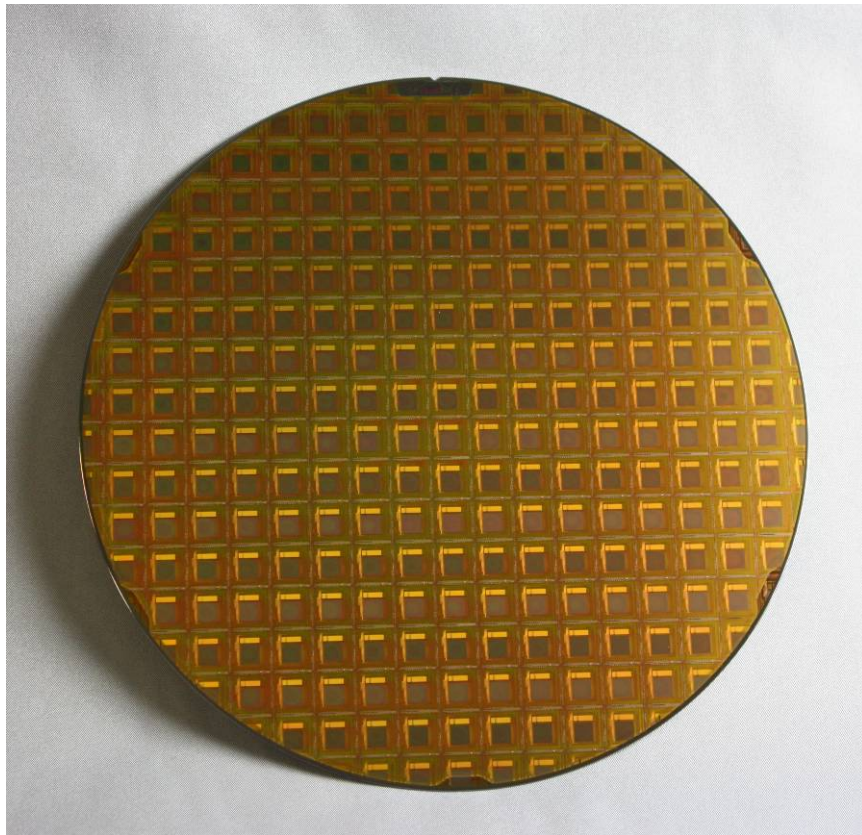
- FoV ± 64 deg
- APS sensor complexity 512 x 512 (but 6 lines each edge unused)
- Storage temp range -60 to +120C (-65 desired)
- Required temperature range -55 to +95C
- Radiation hardness 18yr GEO 1Mrad
5 yr LEO 25krad
- AR coat/Sun Attenuation layer on top glass

To meet these requirements

- Chip
 - APS Pixel pitch 10 μ m
 - Chip 11 x 11.4mm (sensor 5.12x 5.12mm)
 - Sun size on array 18 pixel dia
- Optics
 - Glass Structure 2.5mm glass/Pinhole layer/3.2 mm glass
planarity < 10 arc secs or 0.25 microns over a chip
 - Pinhole to APS pixel alignment 5 μ m
 - Pinhole layer reflectivity <5% internally
 - Rad hard tested to 300KRAD TID
 - Optically matched no air interface at CMOS Glass or Glass/Glass interface
- Packaging/Fabrication
 - Wafer level fabrication
 - Hermetic sealed



Digital Sun Sensor Active Pixel Sensor Development



8" CMOS Wafer & magnified view of Active Pixel Sensor die

Digital Sun Sensor System Level Packaging

Overall packaging

Packaged chip mounted on pcb, fitted in non-hermetic metal enclosure

Overall Package

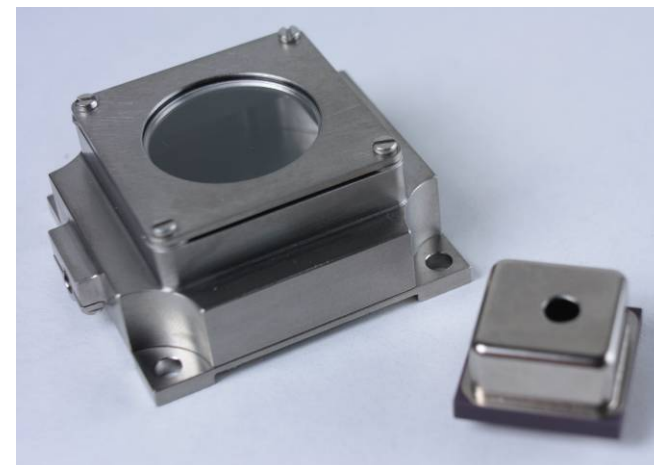
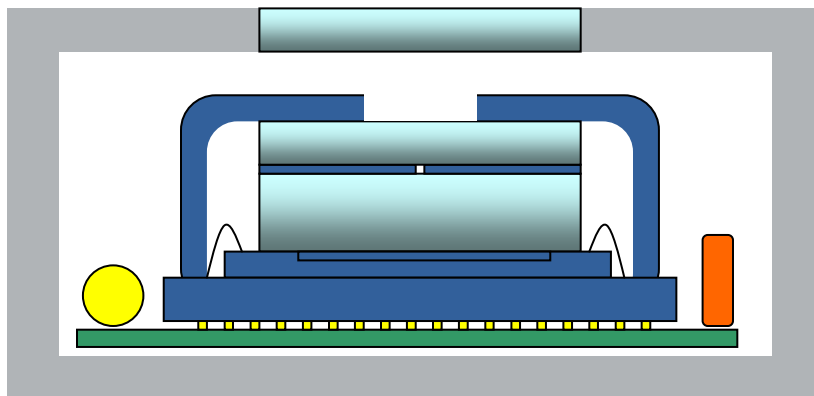
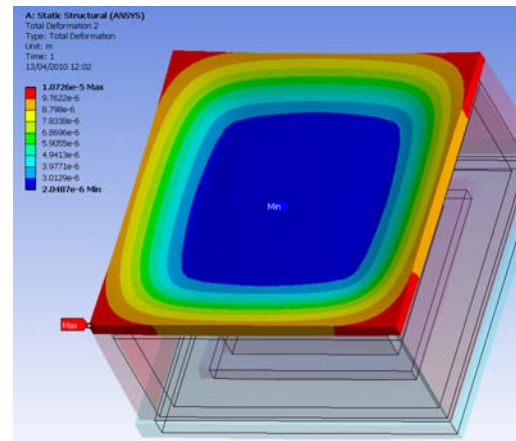
42.0 x 45.0 x 19.8 mm

Overall Mass

65g (expected)

I/O

SpaceWire/RS422



Conclusions

Illustrated Fabrication and Packaging issues for a range of MEMS devices useful to space applications

Despite low volume niche MEMS requirements of space

Often complex /non standard fabrication and packaging techniques required

It is possible to produce and package and qualify MEMS devices for space applications

